IN THE CLAIMS

Please amend claim 1. This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (Currently Amended) A method comprising:

forming a metal oxide semiconductor radio frequency circuit element over a triple well in a substrate;

forming a P-type well in an N-type well formed in the substrate; and

biasing ~~a~~ the P-type well of said triple well through a resistor, wherein the biasing includes applying a bias voltage greater than V_{ss} to the P-type well.

2. (Original) The method of claim 1 including forming an integrated inductor over a triple well.

3. (Cancelled)

4. (Currently Amended) The method of claim ~~3~~, 1 including biasing the N-type and P-type wells through different resistors.

5. (Original) The method of claim 1 including providing a common bias potential to different wells through separate resistors for each well.

7. (Original) The method of claim 5 including biasing said wells through resistors having a resistance greater than one hundred ohms.

8. (Original) The method of claim 7 including forming a complementary metal oxide semiconductor transistor over a triple well and biasing at least one of the wells of said triple well through a resistor.

9. (Original) The method of claim 1 including forming a plurality of triple wells in said substrate and forming a circuit element over each of said triple wells, biasing at least one well of said triple wells through a common potential, each of said potentials being applied to said triple wells through a resistor.

10. (Original) The method of claim 9 including applying a supply potential to said plurality of wells through a resistor.

20. (Currently Amended) A method comprising:

forming a first metal oxide semiconductor radio frequency circuit element over a triple well in a substrate;

forming a P-type well in an N-type well formed in the substrate, the P-type well and the N-type well being associated with the triple well;

biasing ~~a first well of said triple~~ the P-type well through a first resistor with a first bias potential greater than V_{ss};

forming a second metal oxide semiconductor radio frequency circuit element over a second triple well in a substrate; and

biasing a second well of said second triple well through a second resistor coupled to said first bias potential.

21. (Original) The method of claim 20 including coupling the first bias potential to said first and second wells through a common trace to a supply potential.

22. (Original) The method of claim 20 including forming an integrated inductor over the first triple well.

23. (Cancelled)

24. (Original) The method of claim 20 including biasing the N-type and P-type wells through different resistors.

26. (Previously Amended) The method of claim 20 including biasing said wells through resistors having a resistance greater than 100 ohms.

31. (Currently Amended) A method comprising:

forming a metal oxide semiconductor circuit element over a triple well in a substrate, the triple well having a P-type well in an N-type well formed in the substrate;

operating said circuit element at a radio frequency; and

biasing ~~a~~ the P-type well of said triple well through a resistor which acts as a high impedance relative to an impedance associated with a junction capacitance within the triple well, the biasing including applying a voltage greater than V_{ss}.

32. (Original) The method of claim 31 including forming an integrated inductor over said triple well.

33. (Cancelled)

34. (Currently Amended) The method of claim ~~33~~, 31 including biasing the N-type and P-type wells through different resistors.

35. (Original) The method of claim 31 including providing a common bias potential to different wells through separate resistors for each well.

36. (Original) The method of claim 35 including biasing said wells through resistors having a resistance greater than 100 ohms.

37. (Currently Amended) The method of claim 31 including coupling a resistor to the N-type well within said triple well on a P-type substrate so that said resistor acts as a high impedance relative to the impedance associated with the ~~a~~ junction capacitance of the N-type well to the P-type well of the triple well.